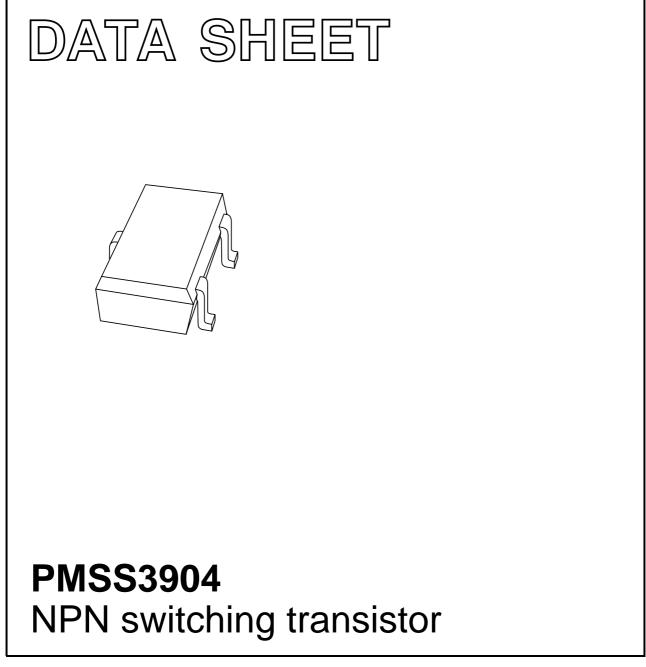
# DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 1997 Sep 03 1999 May 27



## Product data sheet

## NPN switching transistor

#### FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 40 V).

## **APPLICATIONS**

- General purpose switching and amplification
- Telephony and professional communication equipment.

### DESCRIPTION

NPN switching transistor in an SC-70 (SOT323) plastic package. PNP complement: PMSS3906.

## MARKING CODE

| TYPE NUMBER | MARKING CODE <sup>(1)</sup> |  |
|-------------|-----------------------------|--|
| PMSS3904    | *04                         |  |

#### Note

1. \* = - : Made in Hong Kong.

\* = t : Made in Malaysia.

#### PINNING

| PIN | DESCRIPTION |  |
|-----|-------------|--|
| 1   | base        |  |
| 2   | emitter     |  |
| 3   | collector   |  |

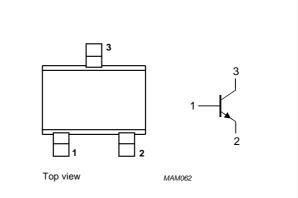


Fig.1 Simplified outline (SC-70; SOT323) and symbol.

## LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

| SYMBOL           | PARAMETER                     | CONDITIONS                            | MIN. | MAX. | UNIT |
|------------------|-------------------------------|---------------------------------------|------|------|------|
| V <sub>CBO</sub> | collector-base voltage        | open emitter                          | -    | 60   | V    |
| V <sub>CEO</sub> | collector-emitter voltage     | open base                             | -    | 40   | V    |
| V <sub>EBO</sub> | emitter-base voltage          | open collector                        | -    | 6    | V    |
| I <sub>C</sub>   | collector current (DC)        |                                       | -    | 100  | mA   |
| I <sub>CM</sub>  | peak collector current        |                                       | -    | 200  | mA   |
| I <sub>BM</sub>  | peak base current             |                                       | _    | 200  | mA   |
| P <sub>tot</sub> | total power dissipation       | $T_{amb} \le 25 \ ^{\circ}C$ ; note 1 | _    | 200  | mW   |
| T <sub>stg</sub> | storage temperature           |                                       | -65  | +150 | °C   |
| T <sub>j</sub>   | junction temperature          |                                       | _    | 150  | °C   |
| T <sub>amb</sub> | operating ambient temperature |                                       | -65  | +150 | °C   |

#### Note

1. Transistor mounted on an FR4 printed-circuit board.

## **PMSS3904**

# NPN switching transistor

## PMSS3904

## THERMAL CHARACTERISTICS

| SYMBOL              | PARAMETER                                   | CONDITIONS | VALUE | UNIT |
|---------------------|---------------------------------------------|------------|-------|------|
| R <sub>th j-a</sub> | thermal resistance from junction to ambient | note 1     | 625   | K/W  |

#### Note

1. Transistor mounted on an FR4 printed-circuit board.

### CHARACTERISTICS

 $T_{amb}$  = 25 °C unless otherwise specified.

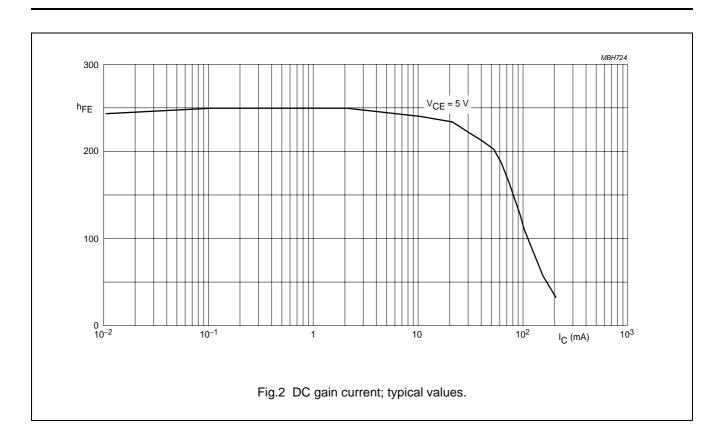
| SYMBOL             | PARAMETER                            | CONDITIONS                                                                     | MIN. | MAX. | UNIT |
|--------------------|--------------------------------------|--------------------------------------------------------------------------------|------|------|------|
| I <sub>CBO</sub>   | collector cut-off current            | I <sub>E</sub> = 0; V <sub>CB</sub> = 30 V                                     | _    | 50   | nA   |
|                    |                                      | I <sub>E</sub> = 0; V <sub>CB</sub> = 30 V; T <sub>j</sub> = 150 °C            | -    | 10   | μA   |
| I <sub>EBO</sub>   | emitter cut-off current              | I <sub>C</sub> = 0; V <sub>EB</sub> = 5 V                                      | _    | 50   | nA   |
| h <sub>FE</sub>    | DC current gain                      | V <sub>CE</sub> = 1 V; see Fig.2                                               |      |      |      |
|                    |                                      | I <sub>C</sub> = 0.1 mA                                                        | 40   | -    |      |
|                    |                                      | $I_{\rm C} = 1  \rm{mA}$                                                       | 70   | -    |      |
|                    |                                      | I <sub>C</sub> = 10 mA                                                         | 100  | 300  |      |
|                    |                                      | I <sub>C</sub> = 50 mA; note 1                                                 | 60   | -    |      |
|                    |                                      | I <sub>C</sub> = 100 mA; note 1                                                | 30   | -    |      |
| V <sub>CEsat</sub> | collector-emitter saturation voltage | I <sub>C</sub> = 10 mA; I <sub>B</sub> = 1 mA                                  | _    | 200  | mV   |
|                    |                                      | $I_{C} = 50 \text{ mA}; I_{B} = 5 \text{ mA}; \text{ note } 1$                 | _    | 300  | mV   |
| V <sub>BEsat</sub> | base-emitter saturation voltage      | I <sub>C</sub> = 10 mA; I <sub>B</sub> = 1 mA                                  | 650  | 850  | mV   |
|                    |                                      | $I_{C} = 50 \text{ mA}; I_{B} = 5 \text{ mA}; \text{ note } 1$                 | _    | 950  | mV   |
| C <sub>c</sub>     | collector capacitance                | I <sub>E</sub> = i <sub>e</sub> = 0; V <sub>CB</sub> = 5 V; f = 1 MHz          | _    | 4    | pF   |
| C <sub>e</sub>     | emitter capacitance                  | $I_{C} = i_{c} = 0; V_{EB} = 0.5 V; f = 1 MHz$                                 | _    | 12   | pF   |
| f <sub>T</sub>     | transition frequency                 | I <sub>C</sub> = 10 mA; V <sub>CE</sub> = 20 V; f = 100 MHz                    | 180  | -    | MHz  |
| F                  | noise figure                         | $I_{C}$ = 100 μA; $V_{CE}$ = 5 V; $R_{S}$ = 1 kΩ<br>f = 10 Hz to 15.7 KHz      | -    | 5    | dB   |
| Switching t        | imes (between 10% and 90% levels     | ); see Fig.3                                                                   |      |      | •    |
| t <sub>on</sub>    | turn-on time                         | I <sub>Con</sub> = 10 mA; I <sub>Bon</sub> = 1 mA;                             | _    | 110  | ns   |
| t <sub>d</sub>     | delay time                           | $I_{Boff} = -1 \text{ mA}; V_{CC} = 3 \text{ V};$<br>$V_{BB} = -1.9 \text{ V}$ | _    | 50   | ns   |
| t <sub>r</sub>     | rise time                            |                                                                                | _    | 60   | ns   |
| t <sub>off</sub>   | turn-off time                        | 1                                                                              | _    | 1200 | ns   |
| t <sub>s</sub>     | storage time                         | 1                                                                              | _    | 1000 | ns   |
| t <sub>f</sub>     | fall time                            | 1                                                                              | _    | 200  | ns   |

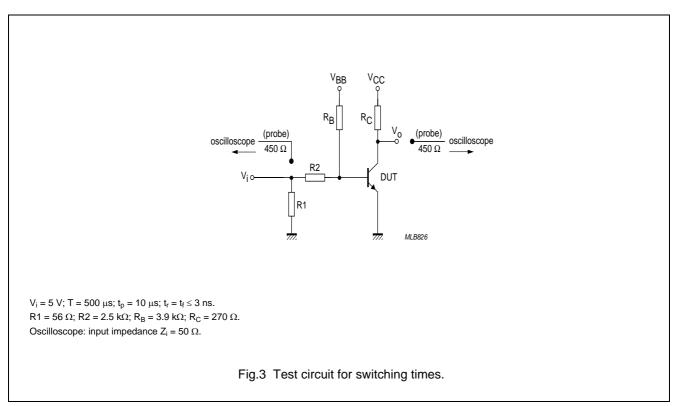
## Note

1. Pulse test:  $t_p \leq 300~\mu\text{s};~\delta \leq 0.02.$ 

PMSS3904

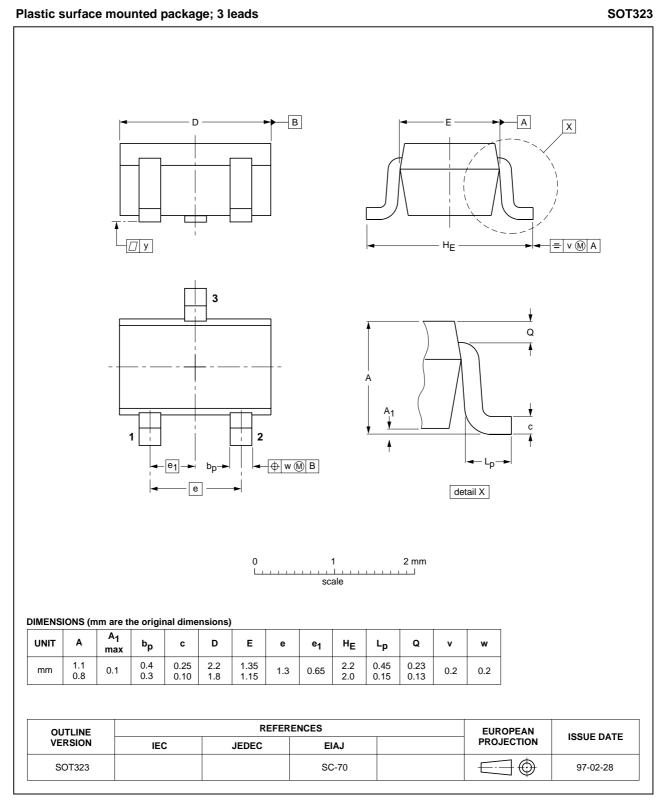
# NPN switching transistor





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### PACKAGE OUTLINE



PMSS3904

## NPN switching transistor

**PMSS3904** 

#### DATA SHEET STATUS

| DOCUMENT<br>STATUS <sup>(1)</sup> | PRODUCT<br>STATUS <sup>(2)</sup> | DEFINITION                                                                            |
|-----------------------------------|----------------------------------|---------------------------------------------------------------------------------------|
| Objective data sheet              | Development                      | This document contains data from the objective specification for product development. |
| Preliminary data sheet            | Qualification                    | This document contains data from the preliminary specification.                       |
| Product data sheet                | Production                       | This document contains the product specification.                                     |

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